

The listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1.-32. (Canceled)

33. (Currently Amended) A method for manufacturing a thin film transistor comprising the steps of:

forming a crystalline semiconductor film by irradiating an energy beam output continuously while scanning the energy beam to a semiconductor film;

forming a gate electrode over the crystalline semiconductor film; and

forming an impurity region in the crystalline semiconductor film using the gate electrode as a mask,

wherein a scanning direction of the beam changes outside an element-forming region formed with the crystalline semiconductor film ~~[[formed]]~~.

34. (Currently Amended) A method for manufacturing a thin film transistor comprising the steps of:

forming a crystalline semiconductor film by irradiating an energy beam output continuously while scanning the energy beam to a semiconductor film;

forming a gate electrode over the crystalline semiconductor film; and

forming an impurity region in the crystalline semiconductor film using the gate electrode as a mask,

wherein the beam is irradiated to an outside of the element-forming region formed with the crystalline semiconductor film ~~formed in positions where~~ when the beam starts to be irradiated ~~and where~~ or the beam ends to be irradiated.

35. (Currently Amended) A method for manufacturing a thin film transistor according to claim 33,

wherein ~~the means for scanning~~ the energy beam is performed by using has a galvanometer mirror or a polygon mirror.

36. (Currently Amended) A method for manufacturing a thin film transistor according to claim 34,

wherein ~~the means for scanning~~ the energy beam is performed by using has a galvanometer mirror or a polygon mirror.

37. (Original) A method for manufacturing a thin film transistor according to claim 33,

wherein the energy beam output continuously is a beam emitted from a laser selected from the group consisting of a YVO₄ laser, a YAG laser, a YLF laser, a YAlO₃ laser, and an Ar laser.

38. (Original) A method for manufacturing a thin film transistor according to claim 34,

wherein the energy beam output continuously is a beam emitted from a laser selected from the group consisting of a YVO₄ laser, a YAG laser, a YLF laser, a YAlO₃ laser, and an Ar laser.

39. (Original) A method for manufacturing a thin film transistor according to claim 33,

wherein the element-forming region is a region where a display device or an integrated circuit is formed.

40. (Original) A method for manufacturing a thin film transistor according to claim 34,

wherein the element-forming region is a region where a display device or an integrated circuit is formed.

41. (Currently Amended) A method for manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film over a substrate;

crystallizing the semiconductor film by irradiating an energy beam output continuously while scanning the energy beam to the semiconductor film;

forming a plurality of semiconductor islands by patterning the crystallized semiconductor film;

forming a first circuit using one of the plurality of semiconductor islands over the substrate [[as an active layer]] ; and

forming a second circuit using another one of the plurality of semiconductor islands over the substrate ~~as the active layer,~~

wherein the energy beam is not irradiated to the first circuit and the second circuit
~~a region irradiated while changing a scanning direction of the energy beam when~~
~~crystallizing the semiconductor film by the energy beam is not included in the~~
~~semiconductor islands constituting the first circuit and the second circuit.~~

42. (Currently Amended) A method for manufacturing a semiconductor device according to claim 41,

wherein the energy beam is irradiated to a region ~~the region irradiated while~~
~~changing the scanning direction of the energy beam is positioned~~ between the first circuit and the second circuit while changing the scanning direction of the energy beam.

43.-44. (Canceled)

45. (Previously Presented) A method for manufacturing a semiconductor device according to claim 33,

wherein the semiconductor device is incorporated into at least one selected from the group consisting of a display, a mobile computer, a game machine, and an electronic book reader.

46. (Previously Presented) A method for manufacturing a semiconductor device according to claim 34,

wherein the semiconductor device is incorporated into at least one selected from the group consisting of a display, a mobile computer, a game machine, and an electronic book reader.

47. (Previously Presented) A method for manufacturing a semiconductor device according to claim 41,

wherein the semiconductor device is incorporated into at least one selected from the group consisting of a display, a mobile computer, a game machine, and an electronic book reader.

48. (New) A method for manufacturing a thin film transistor according to claim 41,

wherein scanning the energy beam is performed by using a galvanometer mirror or a polygon mirror.

49. (New) A method for manufacturing a thin film transistor according to claim 41,

wherein the energy beam output continuously is a beam emitted from a laser selected from the group consisting of a YVO₄ laser, a YAG laser, a YLF laser, a YAlO₃ laser, and an Ar laser.

50. (New) A method for manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film over a substrate;

crystallizing the semiconductor film by irradiating an energy beam output continuously while scanning the energy beam to the semiconductor film;

forming a plurality of semiconductor islands by patterning the crystallized semiconductor film;

forming a first circuit using one of the plurality of semiconductor islands over the substrate; and

forming a second circuit using another one of the plurality of semiconductor islands over the substrate,

wherein the energy beam is not irradiated to the first circuit and the second circuit when the beam starts to be irradiated or the beam ends to be irradiated.

51. (New) A method for manufacturing a thin film transistor comprising the steps of:

forming a crystalline semiconductor film by irradiating an energy beam output continuously while scanning the energy beam to a semiconductor film by moving the semiconductor film and the energy beam relatively;

forming a gate electrode over the crystalline semiconductor film; and

forming an impurity region in the crystalline semiconductor film using the gate electrode as a mask,

wherein a scanning direction of the beam changes outside an element-forming region formed with the crystalline semiconductor film.

52. (New) A method for manufacturing a thin film transistor comprising the steps of:

forming a crystalline semiconductor film by irradiating an energy beam output continuously while scanning the energy beam to a semiconductor film by moving the semiconductor film and the energy beam relatively;

forming a gate electrode over the crystalline semiconductor film; and

forming an impurity region in the crystalline semiconductor film using the gate electrode as a mask,

wherein the beam is irradiated to an outside of the element-forming region formed with the crystalline semiconductor film when the beam starts to be irradiated or the beam ends to be irradiated.

53. (New) A method for manufacturing a thin film transistor according to claim 50,

wherein scanning the energy beam is performed by using a galvanometer mirror or a polygon mirror.

54. (New) A method for manufacturing a thin film transistor according to claim 50,

wherein the energy beam output continuously is a beam emitted from a laser selected from the group consisting of a YVO₄ laser, a YAG laser, a YLF laser, a YAlO₃ laser, and an Ar laser.

55. (New) A method for manufacturing a semiconductor device according to claim 50,

wherein the semiconductor device is incorporated into at least one selected from the group consisting of a display, a mobile computer, a game machine, and an electronic book reader.

56. (New) A method for manufacturing a thin film transistor according to claim 51,

wherein scanning the energy beam is performed by using a galvanometer mirror or a polygon mirror.

57. (New) A method for manufacturing a thin film transistor according to claim 51,

wherein the energy beam output continuously is a beam emitted from a laser selected from the group consisting of a YVO₄ laser, a YAG laser, a YLF laser, a YAlO₃ laser, and an Ar laser.

58. (New) A method for manufacturing a thin film transistor according to claim 51,

wherein the element-forming region is a region where a display device or an integrated circuit is formed.

59. (New) A method for manufacturing a semiconductor device according to claim 51,

wherein the semiconductor device is incorporated into at least one selected from the group consisting of a display, a mobile computer, a game machine, and an electronic book reader.

60. (New) A method for manufacturing a thin film transistor according to claim 52,

wherein scanning the energy beam is performed by using a galvanometer mirror or a polygon mirror.

61. (New) A method for manufacturing a thin film transistor according to claim 52,

wherein the energy beam output continuously is a beam emitted from a laser selected from the group consisting of a YVO₄ laser, a YAG laser, a YLF laser, a YAlO₃ laser, and an Ar laser.

62. (New) A method for manufacturing a thin film transistor according to claim 52,

wherein the element-forming region is a region where a display device or an integrated circuit is formed.

63. (New) A method for manufacturing a semiconductor device according to claim 52,

wherein the semiconductor device is incorporated into at least one selected from the group consisting of a display, a mobile computer, a game machine, and an electronic book reader.